A new analytical and scaleable noise model for HFET

R. Reuter and F.J. Tegude. "A new analytical and scaleable noise model for HFET." 1998 MTT-S International Microwave Symposium Digest 98.1 (1998 Vol. I [MWSYM]): 137-140.

In this paper an analytical noise model for HFET, based on the physical interpretation of the bias dependence of the equivalent intrinsic noise sources, is presented. This model is bias-dependent and scaleable with the gate-geometry and allows the prediction of all noise parameters using two device dependent parameters in a wide bias range.

❑ Return to main document.